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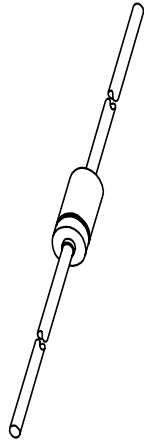
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Kind regards,

Team Nexperia

DATA SHEET



BAS45A Low-leakage diode

Product data sheet
Supersedes data of June 1994

1996 Mar 13

Low-leakage diode

BAS45A

FEATURES

- Continuous reverse voltage: max. 125 V
- Repetitive peak forward current: max. 625 mA
- Low reverse current: max. 1 nA
- Switching time: typ. 1.5 μ s.

DESCRIPTION

Epitaxial medium-speed switching diode with a low leakage current in a hermetically-sealed glass SOD68 (DO-34) package.

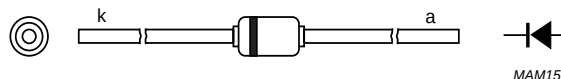


Fig.1 Simplified outline (SOD68; DO-34) and symbol.

APPLICATION

- Low leakage current applications.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		–	125	V
V_R	continuous reverse voltage		–	125	V
I_F	continuous forward current	see Fig.2; note 1	–	250	mA
I_{FRM}	repetitive peak forward current		–	625	mA
I_{FSM}	non-repetitive peak forward current	square wave; $T_j = 25\text{ }^{\circ}\text{C}$ prior to surge; see Fig.4			
		$t_p = 1\text{ }\mu\text{s}$	–	4	A
		$t_p = 1\text{ ms}$	–	1	A
		$t_p = 1\text{ s}$	–	0.5	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ }^{\circ}\text{C}$	–	300	mW
T_{stg}	storage temperature		–65	+175	$^{\circ}\text{C}$
T_j	junction temperature		–	175	$^{\circ}\text{C}$

Note

1. Device mounted on a printed-circuit board without metallization pad.

Low-leakage diode

BAS45A

ELECTRICAL CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_F	forward voltage	see Fig.3 $I_F = 1\text{ mA}$ $I_F = 10\text{ mA}$ $I_F = 100\text{ mA}$	— — —	780 860 1000	mV mV mV
I_R	reverse current	see Fig.5 $V_R = 125\text{ V}$; $E_{\max} = 100\text{ lx}$ $V_R = 30\text{ V}$; $T_j = 125\text{ }^{\circ}\text{C}$; $E_{\max} = 100\text{ lx}$ $V_R = 125\text{ V}$; $T_j = 125\text{ }^{\circ}\text{C}$; $E_{\max} = 100\text{ lx}$ $V_R = 125\text{ V}$; $T_j = 150\text{ }^{\circ}\text{C}$; $E_{\max} = 100\text{ lx}$	— — — —	1 300 500 2	nA nA nA μA
C_d	diode capacitance	$f = 1\text{ MHz}$; $V_R = 0$; see Fig.6	—	4	pF
t_{rr}	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$; $R_L = 100\text{ }\Omega$; measured at $I_R = 1\text{ mA}$; see Fig.7	1.5	—	μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point	8 mm from the body	300	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	lead length 10 mm; note 1	500	K/W

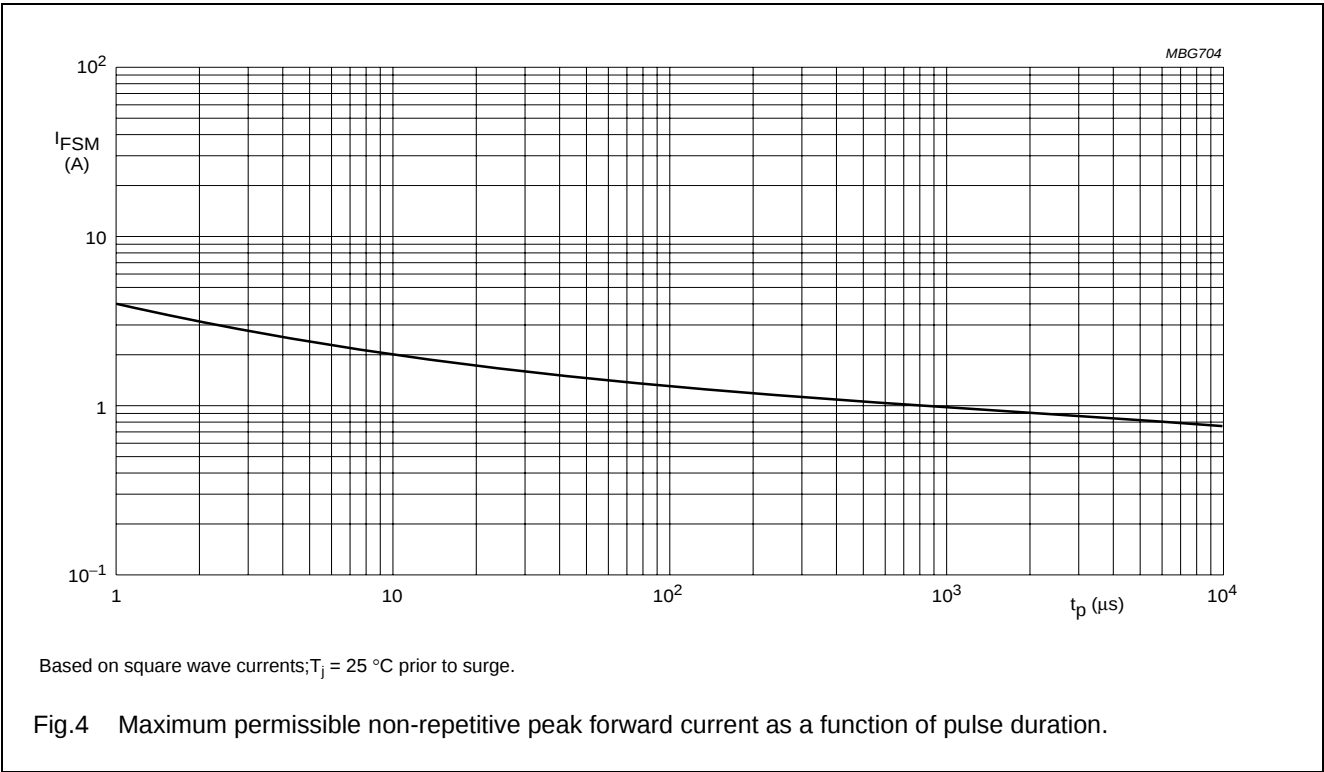
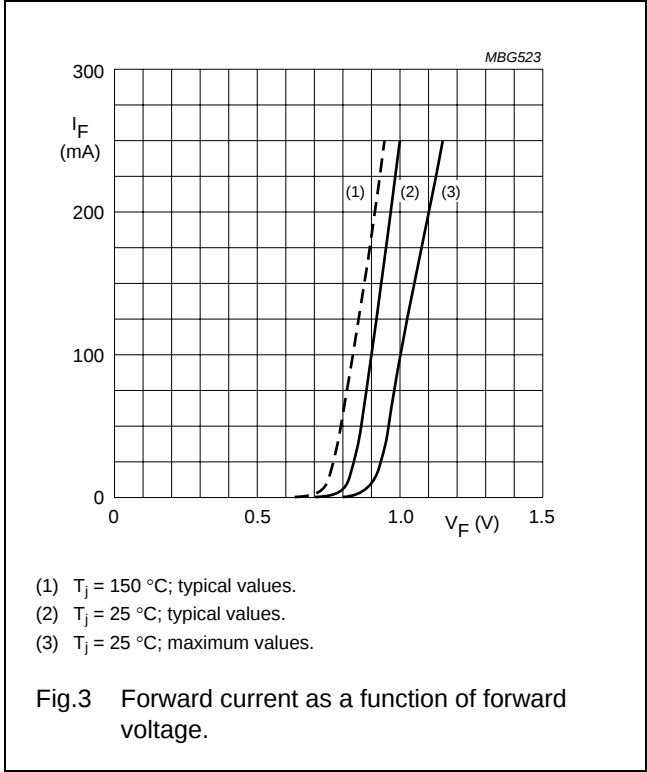
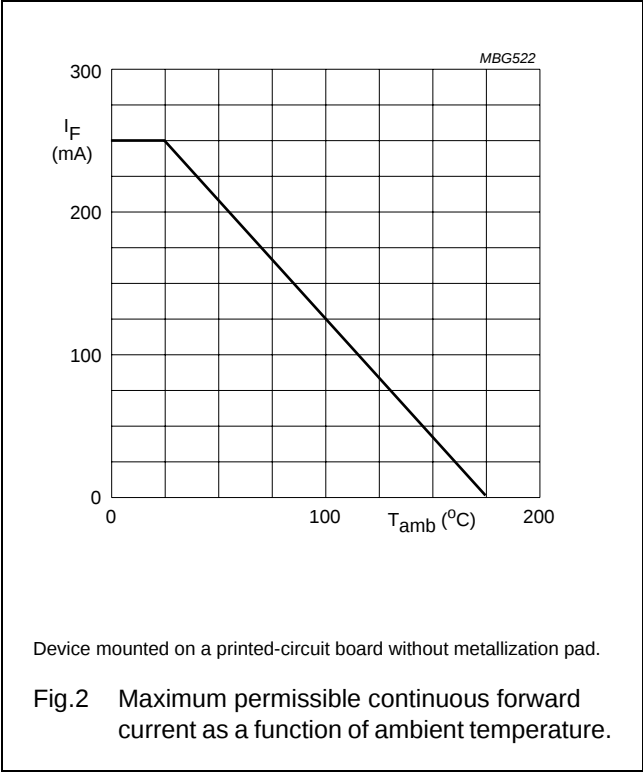
Note

1. Device mounted on a printed-circuit board without metallization pad.

Low-leakage diode

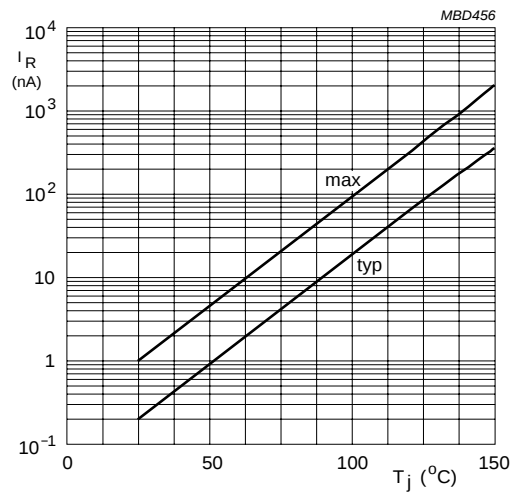
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GRAPHICAL DATA



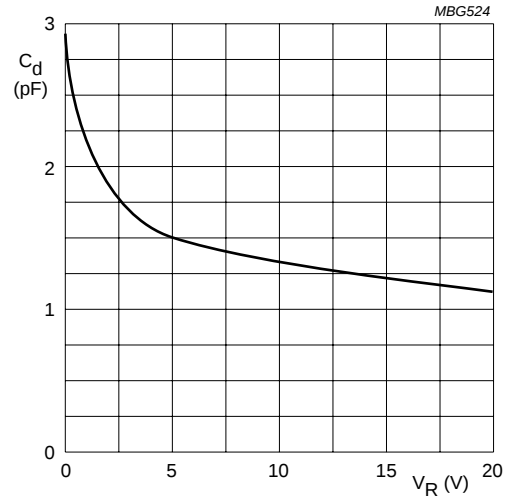
Low-leakage diode

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$V_R = 125$ V.

Fig.5 Reverse current as a function of junction temperature.



$f = 1$ MHz; $T_J = 25$ °C.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

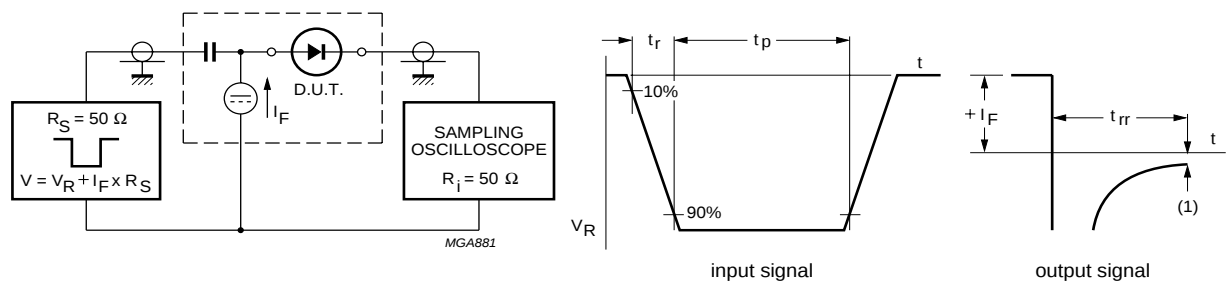
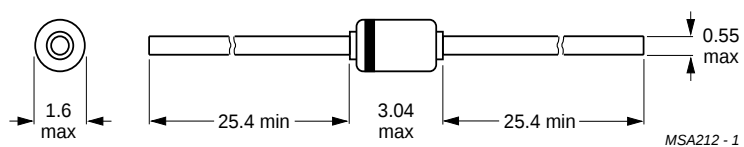


Fig.7 Reverse recovery time test circuit and waveforms.

Low-leakage diode

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PACKAGE OUTLINE



Dimensions in mm.

The black marking band indicates the cathode.

Fig.8 SOD68 (DO-34).

Low-leakage diode

BAS45A

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

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Contact information

For additional information please visit: **<http://www.nxp.com>**

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